

1/1 - (C) FILE CA

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 TI - Excimer laser patterning associated with silylation and oxygne reactiv
 ion etching
 IN - Fukui, Akiyoshi; Tokui, Akira
 PA - Mitsubishi Electric Corp., Japan
 SO - Jpn. Kokai Tokkyo Koho, 4 pp.
 CODEN: JKXXAF
 DT - Patent
 LA - Japanese
 IC - ICM G03F007/038
 ICS G03F007/36;G03F7/38;H01L21/027
 ICA - H01L021-22; H01L021-266
 CC - 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other
 Reprographic Processes)
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	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PN	JP3006566	A	19910114	JP 1989-141765	19890602
PR	JP 1989-141765		19890602		
AB	In patterning of resist for manuf. of semiconductor device, a novolak formed on a substrate is selectively irradiated by excimer laser beam silylated and dry-developed by O plasma reactive ion etching. Thus, a semiconductor substrate was spin-coated with a novolak film, selective irradiated by KrF excimer laser, treated by hexamethyldisilazane in va at high temp., and dry-etched by O plasma to give a precise pattern ha rectangular section.				
ST	patterning resist excimer laser silylation; novolak methylsilylamine silylation dry etching; oxygen plasma novolak resist etching; semiconductor device patterning excimer laser				
IT	Semiconductor devices (patterning of resist for, excimer laser irradsn. and silylation and oxygen plasma reactive ion etching in)				
IT	Phenolic resins, uses and miscellaneous RL: USES (Uses) (novolak, excimer laser resists from, patterning of, silylation and oxygen plasma reactive ion etching in, for semiconductor device)				
IT	Resists (photo-, patterning of, excimer laser irradsn. and silylation and oxy plasma reactive ion etching in)				
IT	999-97-3, Hexamethyldisilazne 34478-34-7, Trimethylsilyldiamine RL: USES (Uses) (photoresist modified by, for patterning of semiconductor device by excimer laser irradsn. and oxygen plasma reactive ion etching)				